METHOD OF IMPROVING A SURFACE

ABSTRACT

The invention relates to a method of improving a surface of a semiconductor substrate, said surface comprises at least partially silicon. It is the object of the present invention to provide a method of improving a surface of a semiconductor substrate, said surface consisting at least partially of silicon, wherein with this method defects present in or on the semiconductor substrate can be really repaired to provide a semiconductor substrate with a high surface quality. This object is solved by a method of the above mentioned type wherein the method comprises a deposition step comprising a selective epitaxial deposition in at least one hole on the surface of said semiconductor substrate.